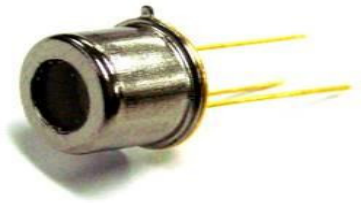
UV-A Sensor

GUVV-T20GD-U

Genuine UV Technology

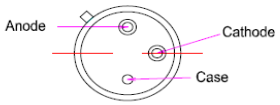
Features

Indium Gallium Nitride Based Material
Schottky-type Photodiode
Photovoltaic Mode Operation
High Responsivity & Low Dark Current



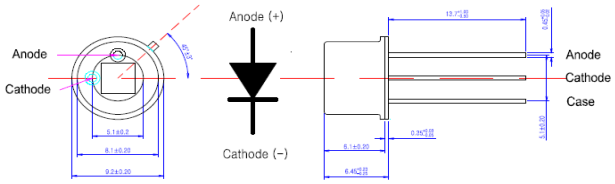
Applications

Full UV Band Monitoring
UV-A Lamp Monitoring
Sterilization Lamp Monitoring



(Bottom View)

Outline Diagrams and Dimensions



(Top View) (Side View)

Absolute Maximum Ratings

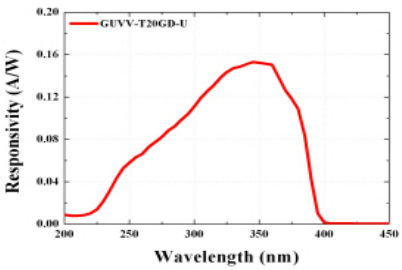
Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	T_{st}	-40	90	℃	
Operating Temperature	T_{op}	-30	85	℃	
Reverse Voltage	$V_{r,\ max.}$		2	V	
Forward Current	$I_{f,max.}$		1	mA	
Optical Source Power Range	P_{opt}	0.001μ	100m	W/㎠	UVA Lamp
Soldering Temperature	T_{sol}		260	℃	within 10 sec.

※Notice: apply to us in the case that Optical Source Power is over 100㎽/㎠.

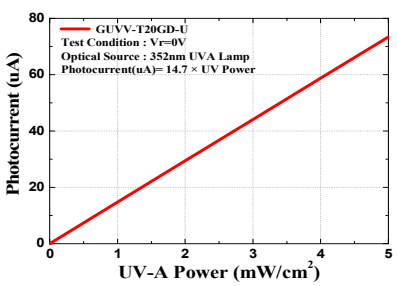
Characteristics (at 25℃)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	I_d			90	nA	Vr = 0.1 V
Photo Current	I_{ph}	13.2	14.7	16.1	μA	UVA Lamp, 1㎽/㎠
Temperature Coefficient	I_{tc}		0.1		%/℃	UVA Lamp
Responsivity	R		0.15		A/W	λ = 352 ㎚, Vr = 0 V
Spectral Detection Range	λ	230		395	㎚	10% of R
Active area			6.894		㎟	

Responsivity Curve



Photocurrent along UV Power



Caution

ESD can damage the device hence please avoid ESD. Insulate the cap of TO-CAN or it can cause malfunction of the device.